

In re Patent Application of:  
**GRANT**  
Serial No. 10/781,977  
Filing Date: **FEBRUARY 19, 2004**

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**In the Claims:**

Claims 1-16 (Cancelled).

17. (Currently Amended) A semiconductor image sensor comprising:

at least one pixel comprising a photosensing portion and a silicide formation prevention coating thereon, said silicide formation prevention coating extending only across the photosensing portion of each pixel and having a thickness to operate as an anti-reflective surface at a desired wavelength range.

18. (Previously Presented) A semiconductor image sensor according to Claim 17, wherein the silicide formation prevention coating has a maximum transmission at a wavelength range of substantially blue light.

19. (Previously Presented) A semiconductor image sensor according to Claim 17, wherein the silicide formation prevention coating has a maximum transmission at a wavelength range of substantially 450nm.

20. (Previously Presented) A semiconductor image sensor according to Claim 17, wherein the silicide formation prevention coating comprises a layer of silicon nitride and a layer of silicon dioxide adjacent thereto.

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21. (Previously Presented) A semiconductor image sensor according to Claim 20, wherein the layer of silicon nitride is substantially 300Å thick and the layer of silicon dioxide is substantially 250Å thick.

22. (Previously Presented) A semiconductor image sensor according to Claim 17, wherein the photosensing portion comprises a photo-diode.

23. (Previously presented) A semiconductor image sensor according to Claim 22, wherein the photo-diode comprises a pinned photo-diode.

24. (Previously presented) A semiconductor image sensor according to Claim 22, wherein the photo-diode comprises a partially pinned photo-diode.

Claims 25-37 (Canceled).

38. (Currently Amended) A partially formed semiconductor image sensor comprising:

at least one pixel comprising a photosensing portion and a silicide formation prevention coating thereon, said silicide formation prevention coating comprising a layer of silicon dioxide and a layer of silicon nitride adjacent thereto;  
said silicon dioxide and silicon nitride layers

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extending only across the photosensing portion of each pixel and  
having thicknesses such that the silicide formation prevention  
coating has a thickness to operate as an anti-reflective surface  
at a desired wavelength range;

an entire surface of each pixel of the partially  
formed image sensor being free of silicide.

Claim 39 (Cancelled).

40. (Previously Presented) A partially formed  
semiconductor image sensor according to Claim 38, wherein the  
silicide formation prevention coating has a maximum transmission  
at a wavelength range of substantially blue light.

41. (Previously Presented) A partially formed  
semiconductor image sensor according to Claim 38, wherein the  
silicide formation prevention coating has a maximum transmission  
at a wavelength range of substantially 450nm.

42. (Previously Presented) A partially formed  
semiconductor image sensor according to Claim 38, wherein the  
layer of silicon nitride is substantially 300Å thick and the  
layer of silicon dioxide is substantially 250Å thick.

43. (Previously Presented) A partially formed  
semiconductor image sensor according to Claim 38, wherein the  
photosensing portion comprises a photo-diode.

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44. (Previously Presented) A partially formed semiconductor image sensor according to Claim 43, wherein the photo-diode comprises a pinned photo-diode.

45. (Previously Presented) A partially formed semiconductor image sensor according to Claim 43, wherein the photo-diode comprises a partially pinned photo-diode.